

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|---|---|------------------|---------|------------------|
| S1 | 4 | (("6653698") or ("6352913")).PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | OFF | 2006/11/16 09:50 |
| S2 | 0 | S1 and "CMOS" and (semiconductor or wafer or substrate) and p-well and n-well and buffer and (gate near4 dielectric) and (metal or conductiv\$4) and etch\$4 and remov\$4 and anneal | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | OFF | 2006/03/17 11:53 |
| S3 | 10 | "CMOS" and (semiconductor or wafer or substrate) and p-well and n-well and buffer and (gate near4 dielectric) and (metal or conductiv\$4) and etch\$4 and remov\$4 and anneal and nitrogen and aluminum | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 12:32 |
| S4 | 1 | "CMOS" and (semiconductor or wafer or substrate) and p-well and n-well and buffer and (gate near4 dielectric) and (metal or conductiv\$4) and etch\$4 and remov\$4 and anneal and nitrogen and aluminum and "sulfuric acid" and "hydrogen peroxide" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 11:55 |
| S5 | 1 | n-mos and p-mos and (semiconductor or wafer or substrate) and p-well and n-well and buffer and (gate near4 dielectric) and (metal or conductiv\$4) and etch\$4 and remov\$4 and anneal and nitrogen and aluminum | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 11:55 |
| S6 | 2243 | n-mos and p-mos | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 12:33 |
| S7 | 176 | n-mos and p-mos and n-well and p-well | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 12:33 |

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| S8 | 6 | n-mos and p-mos and n-well and p-well and ("gate dielectric" near4(semiconductor or wafer or substrate)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 12:34 |
| S9 | 4 | n-mos and p-mos and n-well and p-well and ("gate dielectric" near4(semiconductor or wafer or substrate)) and buffer and etch and metal | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 12:34 |
| S10 | 3 | n-mos and p-mos and n-well and p-well and ("gate dielectric" near4(semiconductor or wafer or substrate)) and buffer and etch and metal and anneal | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 12:35 |
| S11 | 0 | n-mos and p-mos and n-well and p-well and ("gate oxide" near4(semiconductor or wafer or substrate)) and buffer and etch and metal and anneal | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 12:35 |
| S12 | 2 | n-mos and p-mos and n-well and p-well and ("gate oxide" near4(semiconductor or wafer or substrate)) and buffer and etch and metal and anneal | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 12:36 |
| S13 | 156 | ("gate oxide" near4(semiconductor or wafer or substrate)) and buffer and etch and metal and anneal | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 12:36 |
| S14 | 29 | ("gate oxide" near4(semiconductor or wafer or substrate)) and buffer and etch and metal and anneal and p-well and n-well | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 13:22 |
| S15 | 25 | "CMOS" and "aluminum nitride" and "sulfuric acid" and "hydrogen peroxide" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 13:23 |

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| S16 | 1 | "CMOS" and "aluminum nitride" and "sulfuric acid" and "hydrogen peroxide" and "hydrofluoric acid" and anneal and temperature and ("PVD" or "CVD" or "ALD") and (titanium or hafnium or tantalum) and alloy | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 13:25 |
| S17 | 4 | "CMOS" and "aluminum nitride" and "sulfuric acid" and "hydrogen peroxide" and "hydrofluoric acid" and anneal and temperature and ("PVD" or "CVD" or "ALD") and (titanium or hafnium or tantalum) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 13:53 |
| S18 | 1 | "CMOS" and "aluminum nitride" and "sulfuric acid" and "hydrogen peroxide" and "hydrofluoric acid" and anneal and temperature and ("PVD" or "CVD" or "ALD") and (titanium or hafnium or tantalum) and electronegativ\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 13:25 |
| S19 | 921 | hafnium and tantalum and titanium and "CMOS" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 13:53 |
| S20 | 11 | hafnium and tantalum and titanium and "CMOS" and "aluminum nitride" and electronegativ\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 13:54 |
| S21 | 1 | hafnium and tantalum and titanium and "CMOS" and "aluminum nitride" and electronegativ\$4 and n-mos and p-mos | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 13:54 |
| S22 | 9 | hafnium and tantalum and titanium and "CMOS" and "aluminum nitride" and electronegativ\$4 and energy | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 13:57 |
| S23 | 188 | hafnium and "CMOS" and "aluminum nitride" and electronegativ\$4 and energy | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 13:57 |

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| S24 | 9 | hafnium and tantalum and "CMOS" and "aluminum nitride" and electronegativity and energy | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 13:58 |
| S25 | 2180 | "CMOS" and "metal gate" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 13:59 |
| S26 | 4 | "CMOS" and "metal gate" and "aluminum nitride" and electronegativity | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 14:04 |
| S27 | 234 | "aluminum nitride" and electronegativity | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 14:07 |
| S28 | 2 | ("aluminum nitride" near4 electronegativity) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 14:06 |
| S29 | 0 | ("aluminum nitride" near4 electronegativity) and hafnium | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 14:06 |
| S30 | 192 | "aluminum nitride" and electronegativity and hafnium | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 14:07 |
| S31 | 13 | "aluminum nitride" and electronegativity and hafnium and tantalum | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 14:11 |

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| S32 | 10 | "metal gate" and (dielectric or oxide) and electronegativity and hafnium and tantalum | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 14:11 |
| S33 | 2 | "metal gate" and (dielectric or oxide) and electronegativity and hafnium and tantalum and "aluminum nitride" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/17 14:11 |
| S34 | 40177 | CMOS and ((dielectric or oxide or insulat\$4) near9 (semiconductor or substrate or wafer)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 09:52 |
| S35 | 0 | CMOS and ((dielectric or oxide or insulat\$4) near9 (semiconductor or substrate or wafer)) and p-well and n-well and MOSFET and ("aluminum nitride" or "AIN") and (metal near9 "buffer layer") and (etch near9 metal) and anneal\$4 and tmeperature and (PVD or ALD or CVD) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 09:55 |
| S36 | 0 | CMOS and ((dielectric or oxide or insulat\$4) near9 (semiconductor or substrate or wafer)) and p-well and n-well and MOSFET and ("aluminum nitride" or "AIN") and (metal near9 "buffer layer") and (etch near9 metal) and anneal\$4 and temperature and (PVD or ALD or CVD) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 09:56 |
| S37 | 0 | CMOS and ((dielectric or oxide or insulat\$4) near9 (semiconductor or substrate or wafer)) and p-well and n-well and MOSFET and ("aluminum nitride" or "AIN") and metal and (buffer near layer) and (etch near9 metal) and anneal\$4 and temperature and (PVD or ALD or CVD) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 09:57 |

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| S38 | 4 | CMOS and ((dielectric or oxide or insulat\$4) near9 (semiconductor or substrate or wafer)) and p-well and n-well and MOSFET and ("aluminum nitride" or "AlN") and metal and (buffer near layer) and etch and anneal\$4 and temperature and (PVD or ALD or CVD) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:01 |
| S39 | 9 | "5989550" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:01 |
| S40 | 13 | "5989950" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:10 |
| S41 | 1696 | CMOS and (nmos near region) and (pmos near region) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:11 |
| S42 | 506 | CMOS and (nmos near region) and (pmos near region) and n-well and p-well | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:11 |
| S43 | 452 | CMOS and (nmos near region) and (pmos near region) and n-well and p-well and (gate near(dielectric or oxide or insulat\$4)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:12 |
| S44 | 21 | CMOS and (nmos near region) and (pmos near region) and n-well and p-well and (gate near(dielectric or oxide or insulat\$4)) and (metal near alloy\$4) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:12 |

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| S45 | 20 | CMOS and (nmos near region) and (pmos near region) and n-well and p-well and (gate near(dielectric or oxide or insulat\$4)) and (metal near alloy\$4) and (aluminum nitride or "AIN") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:13 |
| S46 | 14 | CMOS and (nmos near region) and (pmos near region) and n-well and p-well and (gate near(dielectric or oxide or insulat\$4)) and (metal near alloy\$4) and (aluminum nitride or "AIN") and (anneal\$4 or thermal or heat\$4) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:13 |
| S47 | 8 | CMOS and (nmos near region) and (pmos near region) and n-well and p-well and (gate near(dielectric or oxide or insulat\$4)) and (metal near alloy\$4) and (aluminum nitride or "AIN") and (anneal\$4 or thermal or heat\$4) and hafnium and tantalum | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:14 |
| S48 | 6 | CMOS and (nmos near region) and (pmos near region) and n-well and p-well and (gate near(dielectric or oxide or insulat\$4)) and (metal near alloy\$4) and (aluminum nitride or "AIN") and (anneal\$4 or thermal or heat\$4) and hafnium and tantalum and (metal near gate) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:27 |
| S49 | 46 | (metal near gate) and (("aluminum nitride" or "AIN") near9 buffer) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:32 |
| S50 | 30 | (metal near gate) and (("aluminum nitride" or "AIN") near9 buffer) and (gate near(dielectric or oxide or insulat\$4)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:32 |
| S51 | 13 | (metal near gate) and (("aluminum nitride" or "AIN") near9 buffer) and (gate near(dielectric or oxide or insulat\$4)) and (metal near9 buffer) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:33 |

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| S52 | 5 | (metal near gate) and (("aluminum nitride" or "AlN") near9 buffer) and (gate near(dielectric or oxide or insulat\$4)) and (metal near9 buffer) and ((anneal or heat) near9 buffer) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:34 |
| S53 | 2 | (metal near gate) and (("aluminum nitride" or "AlN") near9 buffer) and (gate near(dielectric or oxide or insulat\$4)) and (metal near9 buffer) and ((anneal or heat) near9 buffer) and alloy | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:33 |
| S54 | 8 | (metal near gate) and (("aluminum nitride" or "AlN") near9 buffer) and (gate near(dielectric or oxide or insulat\$4)) and (metal near9 buffer) and (anneal or heat) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:34 |
| S55 | 20 | (metal near gate) and (("aluminum nitride" or "AlN") near9 buffer) and (gate near(dielectric or oxide or insulat\$4)) and metal and (anneal or heat) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:40 |
| S56 | 198 | (metal near gate) and ("aluminum nitride" or "AlN") and (gate near(dielectric or oxide or insulat\$4)) and metal and (anneal or heat) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:42 |
| S57 | 122 | (metal near gate) and ("aluminum nitride" or "AlN") and (gate near(dielectric or oxide or insulat\$4)) and metal and (anneal or heat) and cmos | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 10:43 |
| S58 | 35 | (metal near gate) and ("aluminum nitride" or "AlN") and (gate near(dielectric or oxide or insulat\$4)) and metal and (anneal or heat) and cmos and nmos and pmos | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 11:57 |

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| S59 | 3357 | (metal near gate) and CMOS | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 11:13 |
| S60 | 2517 | (metal near gate) and CMOS and (gate near (dielectric or oxide or insulator)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 11:13 |
| S61 | 5 | (metal near gate) and CMOS and (gate near (dielectric or oxide or insulator)) and nmos and pmos and ("aluminum nitride" or "AIN") and electronegativity | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 11:16 |
| S62 | 4 | (metal near gate) and CMOS and (gate near (dielectric or oxide or insulator)) and nmos and pmos and ("aluminum nitride" or "AIN") and electronegativity and hafnium | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 11:24 |
| S63 | 9 | (metal near gate) and CMOS and (gate near (dielectric or oxide or insulator)) and ("aluminum nitride" or "AIN") and electronegativity | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 11:37 |
| S64 | 14 | "6506676" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 11:47 |
| S65 | 5 | (metal near gate) and ("aluminum nitride" or "AIN") and (gate near(dielectric or oxide or insulat\$4)) and metal and (anneal or heat) and cmos and nmos and pmos and electronegativity | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/11/16 11:58 |

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| S66 | 69583 | CMOS and (dielectric or oxide or insulat\$4) near9 (semiconductor or substrate or wafer or carrier) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/22 14:26 |
| S67 | 1896 | CMOS and (dielectric or oxide or insulat\$4) near9 (semiconductor or substrate or wafer or carrier) and (p-well near9 (dielectric or oxide or insulat\$4)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/22 14:27 |
| S68 | 1042 | CMOS and (dielectric or oxide or insulat\$4) near9 (semiconductor or substrate or wafer or carrier) and (p-well near9 (dielectric or oxide or insulat\$4)) and (n-well near9 (dielectric or oxide or insulat\$4)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/22 14:29 |
| S69 | 1 | CMOS and (dielectric or oxide or insulat\$4) near9 (semiconductor or substrate or wafer or carrier) and (p-well near9 (dielectric or oxide or insulat\$4)) and (n-well near9 (dielectric or oxide or insulat\$4)) and ((aluminum near nitride or "AIN") near9 buffer) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/22 14:30 |
| S70 | 10 | CMOS and (dielectric or oxide or insulat\$4) near9 (semiconductor or substrate or wafer or carrier) and (p-well near9 (dielectric or oxide or insulat\$4)) and (n-well near9 (dielectric or oxide or insulat\$4)) and ((aluminum near nitride or "AIN") near9 (dielectric or oxide or insulat\$4)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/22 14:30 |
| S71 | 10 | CMOS and (dielectric or oxide or insulat\$4) near9 (semiconductor or substrate or wafer or carrier) and (p-well near9 (dielectric or oxide or insulat\$4)) and (n-well near9 (dielectric or oxide or insulat\$4)) and ((aluminum near nitride or "AIN") near9 (dielectric or oxide or insulat\$4)) and etch\$4 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/22 14:31 |

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| S72 | 2 | CMOS and (dielectric or oxide or insulat\$4) near9 (semiconductor or substrate or wafer or carrier) and (p-well near9 (dielectric or oxide or insulat\$4)) and (n-well near9 (dielectric or oxide or insulat\$4)) and ((aluminum near nitride or "AIN") near9 (dielectric or oxide or insulat\$4)) and etch\$4 and (metal near9 (aluminum near nitride or "AIN")) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/22 14:45 |
| S73 | 1 | CMOS and (dielectric or oxide or insulat\$4) near9 (semiconductor or substrate or wafer or carrier) and (p-well near9 (dielectric or oxide or insulat\$4)) and (n-well near9 (dielectric or oxide or insulat\$4)) and ((aluminum near nitride or "AIN") near9 (dielectric or oxide or insulat\$4)) and etch\$4 and (metal near9 (aluminum near nitride or "AIN")) and 438/199.ccls. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/03/22 14:45 |
| S74 | 3654 | CMOS and (metal near gate) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/11 13:05 |
| S75 | 275 | CMOS and (metal near gate) and ((aluminum near nitride) or "AIN") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/11 13:06 |
| S76 | 237 | CMOS and (metal near gate) and ((aluminum near nitride) or "AIN") and (metal near (dielectric or oxide or insulat\$4)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/11 13:06 |
| S77 | 12 | CMOS and (metal near gate) and ((aluminum near nitride) or "AIN") and (metal near (dielectric or oxide or insulat\$4)) and electronegativity | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/11 13:11 |

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| S78 | 12 | (CMOS or nmos or pmos)and (metal near gate) and ((aluminum near nitride) or "AIN") and (metal near (dielectric or oxide or insulat\$4)) and electronegativity | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/11 13:13 |
| S79 | 12 | (CMOS or "Complementary Metal Oxide Semiconductor")and (metal near gate) and ((aluminum near nitride) or "AIN") and (metal near (dielectric or oxide or insulat\$4)) and electronegativity | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/11 13:14 |
| S80 | 15 | (CMOS or "Complementary Metal Oxide Semiconductor")and (metal near (gate or electrode)) and ((aluminum near nitride) or "AIN") and (metal near (dielectric or oxide or insulat\$4)) and electronegativity | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/11 13:14 |
| S81 | 15 | (CMOS or "Complementary Metal Oxide Semiconductor")and (metal near (gate or electrode)) and ((aluminum near nitride) or "AIN") and (metal near (dielectric or oxide or insulat\$4)) and (electronegativity or electronegative) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/11 13:17 |
| S82 | 244 | (CMOS or "Complementary Metal Oxide Semiconductor")and (metal near (gate or electrode)) and ((aluminum near nitride) or "AIN") and (metal near (dielectric or oxide or insulat\$4)) and alloy | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/11 13:23 |
| S83 | 28 | (CMOS or "Complementary Metal Oxide Semiconductor") and ((aluminum near nitride) or "AIN") and alloy and electronegativ\$4 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/11 13:21 |
| S84 | 125 | ((aluminum near nitride) or "AIN") and alloy and electronegativ\$4 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/11 13:21 |

EAST Search History

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| S85 | 28 | ((aluminum near nitride) or "AlN") and alloy and electronegativ\$4 and (CMOS) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/11 13:21 |
| S86 | 532552 | (CMOS or "Complementary Metal Oxide Semiconductor")and (metal near (gate or electrode)) and ((aluminum near nitride) or "AlN") and (metal near (dielectric or oxide or insulat\$4)) and alloy and ("Hf" or hafnium) or ("Ta" or tantalum) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/11 13:24 |
| S87 | 131 | (CMOS or "Complementary Metal Oxide Semiconductor")and (metal near (gate or electrode)) and ((aluminum near nitride) or "AlN") and (metal near (dielectric or oxide or insulat\$4)) and alloy and ("Hf" or hafnium) and ("Ta" or tantalum) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/11 13:24 |
| S88 | 4 | (CMOS or "Complementary Metal Oxide Semiconductor")and (metal near (gate or electrode)) and ((aluminum near nitride) or "AlN") and (metal near (dielectric or oxide or insulat\$4)) and alloy and ("Hf" or hafnium) and ("Ta" or tantalum) and electronegativ\$4 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/11 13:25 |
| S89 | 15297 | (metal near gate) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/06/14 09:06 |
| S90 | 3791 | (metal near gate) and CMOS | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/06/14 09:06 |
| S91 | 3546 | (metal near gate) and CMOS and (gate near9 (dielectric or oxide or insulat\$4)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/06/14 09:07 |

EAST Search History

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| S92 | 7 | (metal near gate) and CMOS and (gate near9 (dielectric or oxide or insulat\$4)) and alloy and ("AIN" or (aluminum near nitride)) and electronegativ\$4 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/06/14 09:08 |
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